

The employ of manganese oxide to improve the selectivity of gas sensitive SnO_x films

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To improve the selectivity of gas-sensitive SnO_x films, SnO_x/MnO_y composite structures were obtained in which manganese oxide plays the role of a NO₂ sorbing filter. The microstructure and chemical composition of the films were characterized using scanning electron microscopy and X-ray photoelectron spectroscopy. The structures were tested to detect 5 ppm NO₂ at room temperature. The sensory response of SnO_x films in the presence of NO₂ decreases by 16 times after coating the MnO_y filter layer.

Keywords: filters, microsensors, manganese oxide, tin dioxide.

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The task of obtaining interconnected multilevel structures on porous media with layers of various morphologies obtained in a single technological process and their subsequent functionalization is of great interest in micro- and nanosensors. In particular, it is possible to create a vertically integrated sensor structure, including transport layers for the analyte gas, filtering layers, sorbing and sensitive layers.

Given the low cost and miniaturization of microsensors compared to gas analyzers and the possibility of using sensor networks to multiply information, chemical microsensors may represent a cheaper alternative for detecting gases. Microsensors are based on physico-chemical principles and are usually sensitive enough for most applications, but their low selectivity is a major limitation for the selective detection of a single component. The use of nonstoichiometric tin dioxide films as a sensing element is limited by their selectivity and stability as a result of morphological changes in the sensing material (grain growth) or chemical irreversible reactions with a number of gases. Active filters can be used to improve the selectivity of SnO_x films. SnO_x films are easily applied to porous silicon substrates by various methods, which makes it possible to create a vertically integrated sensor structure. A number of papers [1,2] show that MnO₂ layers can be used as filters for SnO_x and WO₃ films, in particular for ozone. Nanomaterials based on manganese oxide in various polymorphic modifications and degrees of oxidation are used as sensitive elements for detecting mainly reducing gases, such as H₂, NH₃, C₂H₄, With₂H₅OH, CH₃CN, CO. As a rule, the sizes of manganese oxide nanoparticles for sensitive elements are 20–200 nm [3–8]. For MnO₂ used as active filters, the particle sizes were on the order of units of micrometers [2].

The development of film technologies for applying functional layers is the most important for the integration and

creation of multi-sensor devices. This paper shows the possibility of obtaining filters based on MnO_y as a nitrogen dioxide sorbent applied to SnO_x films.

MnO_y layers were obtained by thermal decomposition of manganese nitrate in ethyl alcohol and deposited on pre-formed SnO_x films on citallic and silicon substrates. SnO_x was obtained by chemical vapor-phase deposition [9]. A layer of Mn(NO₃)₂ solution in 0.14 M ethyl alcohol was first applied to the substrates. The samples were then dried at room temperature. Then the substrates were slowly heated to a temperature of 350°C, and kept at this temperature for 5 min. Next, the samples were cooled to room temperature, and the manganese nitrate solution was applied in layers again in the same mode until a sufficiently noticeable and durable layer of MnO_y was formed.

The morphology and elemental composition of SnO_x/MnO_y structures were studied using scanning electron microscopy (SEM) and energy dispersion analysis (EDA) using Jeol JSM-6610-LV scanning electron microscope with an energy dispersion analyzer Inca-XAct. The SEM images of SnO_x/MnO_y samples obtained in the secondary electron registration mode show a SnO_x layer having a granular structure with a grain size of ~ 100 nm, which is partially covered by a layer manganese oxide. The grain size of the manganese oxide layer varies in the range of 0.5–2 μm. According to EDA data, the concentration of manganese is 0.2 at% in the areas where the granular structure is observed (Figure 1, point 1), while this value is 3.4 and 1.9 at%, respectively, in the upper layer (Figure 1, points 2 and 3). The tin concentration at these points is 5.5, 4.0, and 4.9 at%, respectively. Lighter contrast at points 2 and 3 compared to point 1 is explained by the high resistivity of manganese oxide compared to the resistivity of tin oxide.

The chemical composition of the surface of MnO_y layers deposited on SnO_x films stained with Si by X-ray photoelectron spectroscopy (XPS) was studied. Figure 2

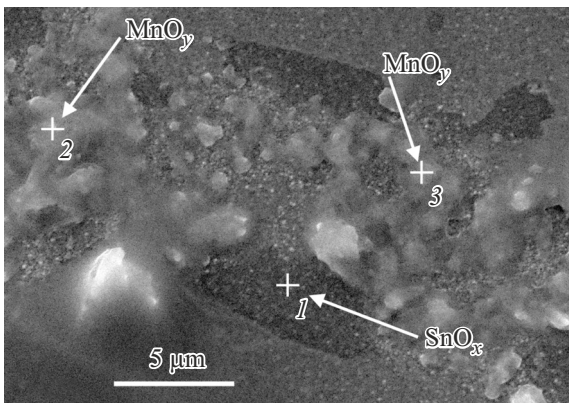


Figure 1. REM image of $\text{SnO}_x/\text{MnO}_y$ layer. Crosses mark the points where the elemental composition was analyzed using the EDA method.

shows an overview of the XPS spectrum of $\text{SnO}_x/\text{MnO}_y$ sample before and after exposure in NO_2 pairs. The spectrum of the initial sample contains photoelectron lines of manganese ($\text{Mn } 2p$, $\text{Mn } 3s$), oxygen ($\text{O } 1s$), tin ($\text{Sn } 3d$) and carbon ($\text{C } 1s$). The presence of carbon is associated with the adsorption of pollutants during the storage of the sample in the air. Exposure to an atmosphere saturated with nitrogen dioxide slightly changes the appearance of the viewing spectrum. A nitrogen line ($\text{N } 1s$) is detected in the spectrum, indicating sorption of NO_2 on the surface of $\text{SnO}_x/\text{MnO}_y$ sample. Also, a change of the shape of the manganese peak ($\text{Mn } 2p$) is visible on the overview XPS spectrum. The shape of $\text{Mn } 2p$ peak on the spectrum before exposure in NO_2 has 2 maxima, which correspond to $\text{Mn } 2p_{1/2}$ and $\text{Mn } 2p_{3/2}$ lines [10]. In this case, the $\text{Mn } 2p_{3/2}$ line has a higher intensity than $\text{Mn } 2p_{1/2}$ line. This type of spectrum is typical for slightly oxidized

manganese. Exposure to a saturated atmosphere NO_2 leads to an equalization of the intensities of $\text{Mn } 2p_{1/2}$ and $\text{Mn } 2p_{3/2}$ components, which is a sign of manganese oxidation. The analysis of the core $\text{Mn } 3s$ spectrum also confirms this assumption. $\text{Mn } 3s$ XPS of spectrum of the initial $\text{SnO}_x/\text{MnO}_y$ sample has 2 components with bond energies of 89.6 eV and 83.5 eV. The energy distance between the maxima of $\text{Mn } 3s$ XPS of the spectrum of the initial sample is 6.1 eV, which corresponds to the state of MnO . Exposure to NO_2 atmosphere leads to a shift of the maximum of the low-energy component to 84.2 eV and a decrease of the energy distance between the maxima to 5.4 eV, which corresponds to higher degrees of oxidation of $\text{Mn}_2\text{O}_3 - \text{MnO}_2$ [11].

The following table shows the results of quantitative elemental analysis carried out using the review XPS spectra of $\text{SnO}_x/\text{MnO}_y$ sample using elemental sensitivity coefficients. The analysis results show an increase of nitrogen concentration to 7.6 at% on the sample surface after exposure to NO_2 vapors, which also indicates sorption of nitrogen dioxide molecules by manganese oxide.

Studies of gas sensitivity at 5 ppm of NO_2 were conducted at room temperature. SnO_x film on a citall substrate was used as a gas-sensitive element.

The response of a resistive gas-sensitive element was compared before and after application of the MnO_y sorbing layer. The resistance of the resistive gas-sensitive element was estimated from linear volt-ampere characteristics, which were measured using an Agilent E4980A LCR meter. The response S of the sensor element was calculated as $S = [(R_g - R_0)/R_0] \cdot 100\%$, where R_g — the resistance of the element after exposure to gas, R_0 — the initial resistance of the element before exposure to gas.

The results of gas sensitivity testing are shown in Figure 3, *a*. The sensor response at an exposure to 5 ppm of NO_2 for SnO_x films before application of the film sorbent

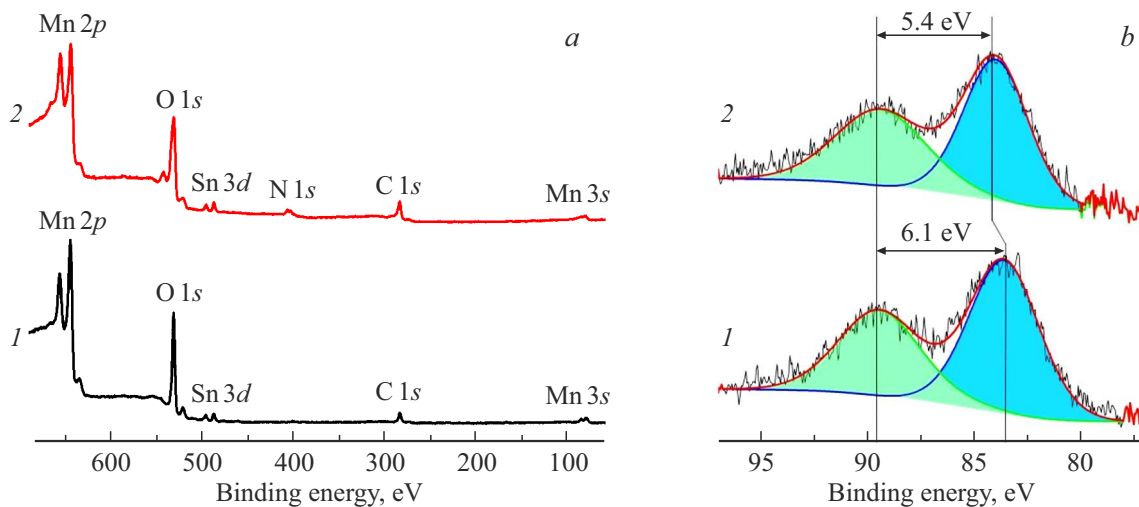


Figure 2. XPS spectra of $\text{SnO}_x/\text{MnO}_y$ sample: *a* — overview spectrum; *b* — $\text{Mn } 3s$; *1* — spectrum of the initial sample, *2* — spectrum of the sample after exposure in NO_2 .

Chemical composition of SnO_x/MnO_y sample before and after exposure to NO₂* vapors

Sample	[Mn]	[C]	[N]	[Sn]	[O]
SnO _x /MnO _y	22	24.5	–	0.5	53
SnO _x /MnO _y after NO ₂	20	21.3	7.6	0.9	50.2

Note. * All results are in atom per cent.

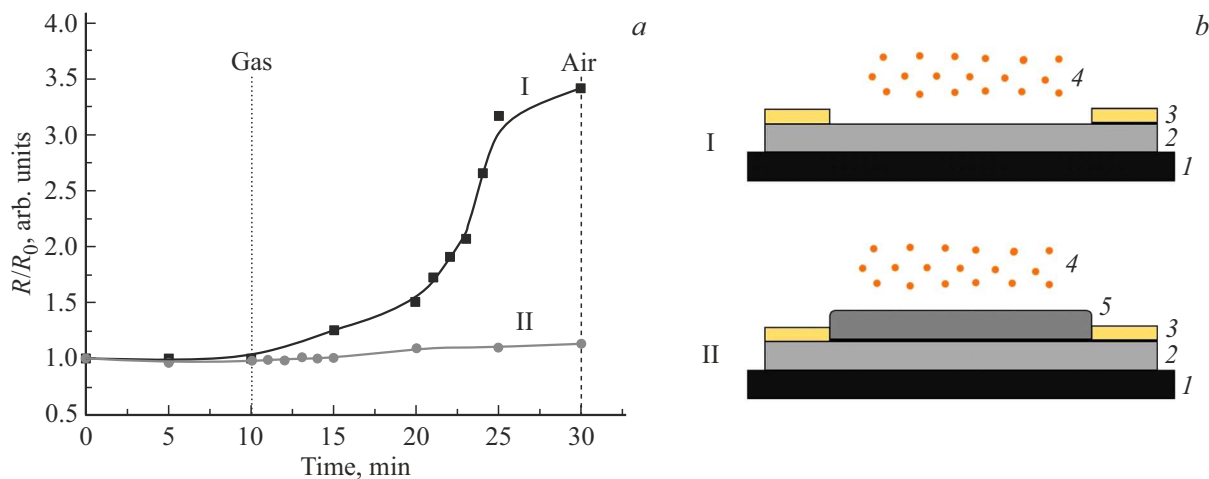


Figure 3. Change of the ratio of the resistance of the gas-sensitive element to the initial resistance at exposure to 5 ppm of NO₂ (a) and the schemes of the test structures (b): I — SnO_x, II — SnO_x/MnO_y; 1 — substrate, 2 — SnO_x layer, 3 — metal contacts, 4 — NO₂ molecules, 5 — MnO_y layer.

was 240%, it was 15% after application of the film sorbent. Comparing the results of electrophysical measurements with the XPS data, it can be said that the sorption of NO₂ molecules is accompanied by the oxidation of MnO to Mn₂O₃ and MnO₂.

The SEM data indicate that the surface of the sensor element (SnO_x) is partially covered with a layer of manganese oxide. According to the literature data in Ref. [1,2], this layer configuration makes it possible to efficiently sorb molecules of oxidizing gases. The obtained results of electrophysical studies indicate the absorption of nitrogen dioxide by the MnO_y film. Studies of the surface of the MnO_y layer before and after exposure in NO₂ vapors showed a change of the chemical state of manganese. A shift of the XPS components of the Mn_{3s} spectrum is observed, which indicates the oxidation of the manganese layer. At the same time, quantitative elemental analysis indicates an increase of nitrogen concentration in the surface layers of the SnO_x/MnO_y structure. The results obtained allow making a conclusion that the interaction of NO₂ vapors and the MnO_y layer results in effective sorption of nitrogen dioxide molecules, which is accompanied by oxidation of the near-surface layers of MnO_y.

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Conflict of interest

The authors declare that they have no conflict of interest.

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